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May 2009

FDG6317NZ

Dual 20v N-Channel PowerTrench MOSFET

General Description

This dual N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized use in small switching regulators, providing an extremely low R_{DS(ON)} and gate charge (Q_G) in a small package.

Applications

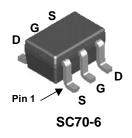
- DC/DC converter
- · Power management
- · Load switch
- · RoHS Compliant

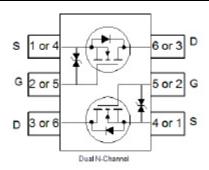


Features

- 0.7 A, 20 V. $R_{DS(ON)}$ = 400 m Ω @ V_{GS} = 4.5 V $R_{DS(ON)} = 550 \text{ m}\Omega @ V_{GS} = 2.5 \text{ V}$
- · Gate-Source Zener for ESD ruggedness (1.6kV Human Body Model). (Note 3)
- · Low gate charge
- High performance trench technology for extremely
- Compact industry standard SC70-6 surface mount package







The pinouts are symmetrical; pin 1 and pin 4 are interchangeable.

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		20	V
V _{GSS}	Gate-Source Voltage		± 12	V
I _D	Drain Current - Continuous	(Note 1)	0.7	Α
	– Pulsed		2.1	
P _D	Power Dissipation for Single Operation	(Note 1)	0.3	W
T _J , T _{STG}	Operating and Storage Junction Temperati	ure Range	-55 to +150	°C

Thermal Characteristics

Rela	Thermal Resistance, Junction-to-Ambient	(Note 1)	415	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.67	FDG6317NZ	7"	8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = 250 \mu\text{A}$	20			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		13		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 16 V, V _{GS} = 0 V			1	μΑ
I _{GSS}	Gate-Body Leakage	$V_{GS} = \pm 12 \text{ V}, \ V_{DS} = 0 \text{ V}$			± 10	μΑ
I _{GSS}	Gate-Body Leakage	$V_{GS} = \pm 4.5 \text{ V}, V_{DS} = 0 \text{ V}$			± 1	μΑ
On Char	acteristics (Note 2)			•	•	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.6	1.2	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-2		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 0.7 \text{ A}$ $V_{GS} = 2.5 \text{ V}, I_D = 0.6 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 0.7 \text{ A}, T_J = 125 ^{\circ}\text{C}$		300 450 390	400 550 560	mΩ
I _{D(on)}	On–State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	1			Α
g _{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, \qquad I_{D} = 0.7 \text{ A}$		1.8		S
Dynamic	Characteristics		•			
C _{iss}	Input Capacitance	V _{DS} = 10 V, V _{GS} = 0 V,		66.5		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		19		pF
C _{rss}	Reverse Transfer Capacitance			10		pF
R_G	Gate Resistance	$V_{GS} = 15 \text{ mV}, f = 1.0 \text{ MHz}$		5.8		Ω
Switching	Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, I_{D} = 1 \text{ A},$		5.5	11	ns
t _r	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		7	15	ns
$t_{d(off)}$	Turn-Off Delay Time			7.5	15	ns
t _f	Turn-Off Fall Time			2.5	5	ns
Qg	Total Gate Charge	$V_{DS} = 10 \text{ V}, I_{D} = 0.7 \text{ A},$		0.76	1.1	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 4.5 V		0.18		nC
Q_{gd}	Gate-Drain Charge			0.20		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Sour	_			0.25	Α
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \qquad I_S = 0.25 \text{ A (Note 2)}$		0.8	1.2	V
t _{rr}	Diode Reverse Recovery Time	$I_F = 0.7 \text{ A}, \qquad d_{iF}/d_t = 100 \text{ A}/\mu\text{s}$		8.3		nS
Q _{rr}	Diode Reverse Recovery Charge			1.2		nC

Notes

^{1.} R_{8JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{8JC} is guaranteed by design while R_{8JA} is determined by the user's board design. R_{8JA} = 415°C/W when mounted on a minimum pad .

^{2.} Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

^{3.} The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics

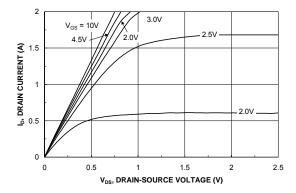


Figure 1. On-Region Characteristics.

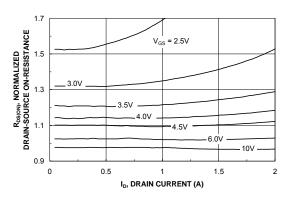


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

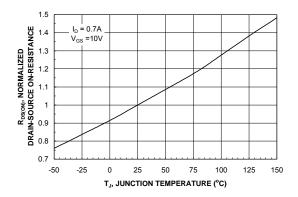


Figure 3. On-Resistance Variation with Temperature.

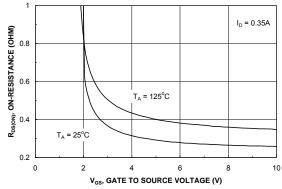


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

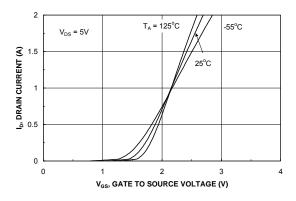


Figure 5. Transfer Characteristics.

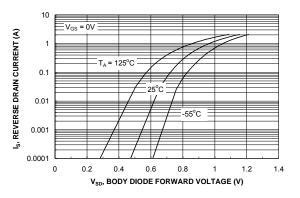


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

f = 1MHz

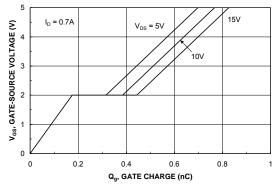
 $V_{GS} = 0 V$

20

 C_{iss}

15

Typical Characteristics



25 C_{rss} 0 0 10 V_{DS}, DRAIN TO SOURCE VOLTAGE (V)

100

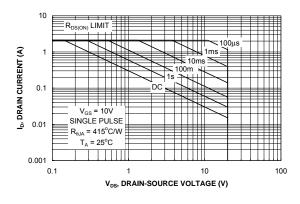
CAPACITANCE (pF)

50

Figure 7. Gate Charge Characteristics.



 $\mathsf{C}_{\mathsf{oss}}$



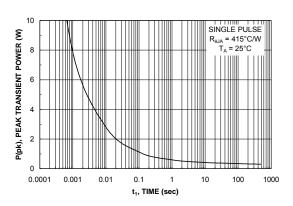


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

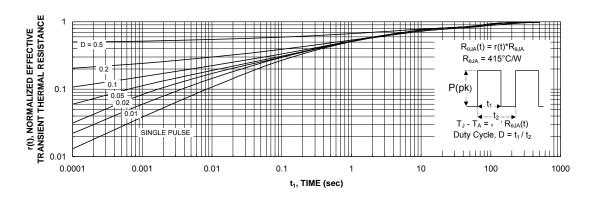


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1. Transient thermal response will change depending on the circuit board design.





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